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Sommario/riassunto

This book delves into the advanced design and application of ultra low-power semiconductor devices, with a focus on transistors such as MOSFETs and TFETs. It explores various aspects of these technologies, including leakage reduction techniques, material properties, and performance comparisons. The book also examines the potential applications of these devices in low-power electronics, memory devices, and analog/RF circuits. Aimed at professionals and researchers in the field of electronics engineering, it provides insights into the challenges and future prospects of semiconductor device technology.